

1 **ABSTRACT OF THE DISCLOSURE**

2 The invention encompasses a method of forming an oxide region
3 over a semiconductor substrate. A nitrogen-containing layer is formed
4 across at least some of the substrate. After the nitrogen-containing layer
5 is formed, an oxide region is grown from at least some of the substrate.
6 The nitrogen of the nitrogen-containing layer is dispersed within the
7 oxide region. The invention also encompasses a method of forming a
8 pair of transistors associated with a semiconductor substrate. A substrate
9 is provided. A first region of the substrate is defined, and additionally
10 a second region of the substrate is defined. A first oxide region is
11 formed which covers at least some of the first region of the substrate,
12 and which does not cover any of the second region of the substrate.
13 A nitrogen-comprising layer is formed across at least some of the first
14 oxide region and across at least some of the second region of the
15 substrate. After the nitrogen-comprising layer is formed, a second oxide
16 region is grown from the second region of the substrate. A first
17 transistor gate is formed over the first oxide region, and a second
18 transistor gate is formed over the second oxide region.

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